

2020년 2월 14일(금), 10:45~12:30

Room C (사파이어 I, 5층)

H. Display and Imaging Technologies 분과

[FC2-H] Oxide Thin-Film Transistors

FC2-H-1 10:45~11:15	[초청] Optoelectronics based on the Quantum-dots and Oxide Semiconductors Seong Jun Kang <i>Department of Advanced Materials Engineering for Information and Electronics, Kyung Hee University</i>
FC2-H-2 11:15~11:30	Impact of Oxidants on Formation of HfO₂ Gate Insulator Prepared by Atomic-layer Deposition for In-Ga-Zn-O Thin Film Transistor Se-na Choi and Sung-min Yoon <i>Department of Advanced Materials Engineering for Information and Electronics, Kyung Hee University</i>
FC2-H-3 11:30~11:45	Thin Film Transistor Characteristics of In-Sn-Ga-O Semiconductor at Low Temperature. Changyong Oh and Bo Sung Kim <i>Department of Applied Physics, Korea University</i>
FC2-H-4 11:45~12:00	Effects of Lateral Carrier Diffusion and Source-Drain Parasitic Resistance in Self-Aligned Top-Gate Coplanar InGaZnO Thin-Film Transistors Dae-hwan Kim ¹ , Sae-young Hong ¹ , Hee-joong Kim ¹ , Ha-yun Jeong ¹ , Sang-hun Song ¹ , In-tak Cho ² , Jiyong Noh ² , Hyun Soo Shin ² , Kwon-shik Park ² , Hyun Chul Choi ² , In Byeong Kang ² , and Hyuck-in Kwon ¹ <i>¹School of Electrical and Electronics Engineering, Chung-Ang University, ²Research and Development Center, LG Display Co., Ltd.</i>
FC2-H-5 12:00~12:15	The Electrical Performance Difference of TFTs Using SiO_x Gate Insulator Deposited by PECVD and PEALD with DIPAS Precursor Seokgoo Jeong ¹ , Wanho Choi ² , Hyun-jun Jeong ² , Kyungrok Kim ² , Hyun-mo Lee ² , Suhwan Choi ¹ , and Jin-seong Park ^{1,2} <i>¹Division of Nanoscale of Semiconductor Engineering, Hanyang University, ²Division of Materials Science and Engineering, Hanyang University</i>
FC2-H-6 12:15~12:30	Importance of Substrate Thickness Control on Electrical and Mechanical Operation Robustness of Flexible InGaZnO Thin Film Transistors Hye-won Jang and Sung-min Yoon <i>Department of Advanced Materials Engineering for Information and Electronics, Kyung Hee University</i>